



# A 1024-Ch GFET 10-bit 5-kHz 36- $\mu$ W Read-Out Integrated Circuit for Brain $\mu$ ECoG

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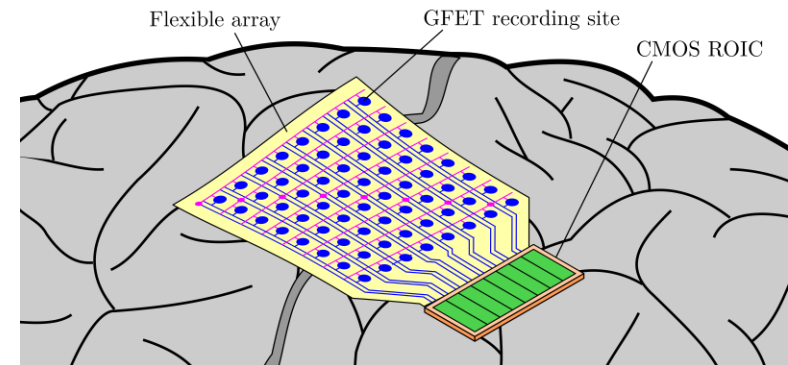
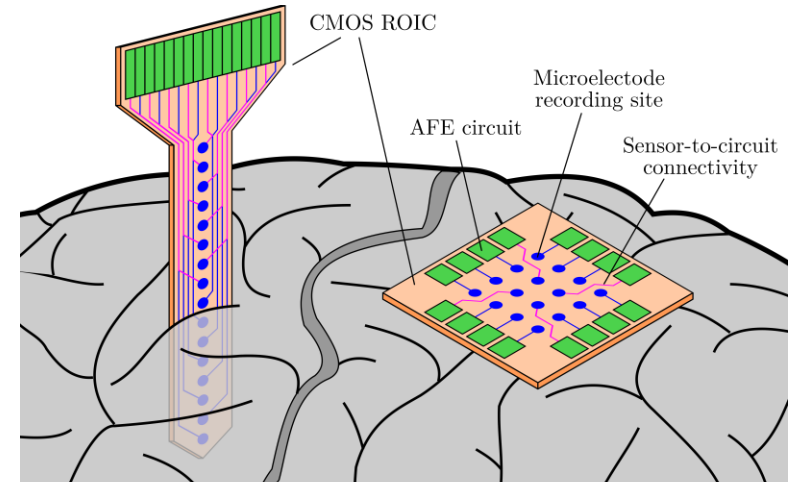
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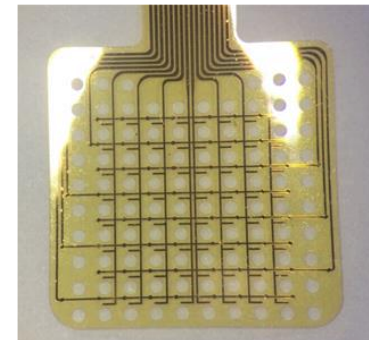
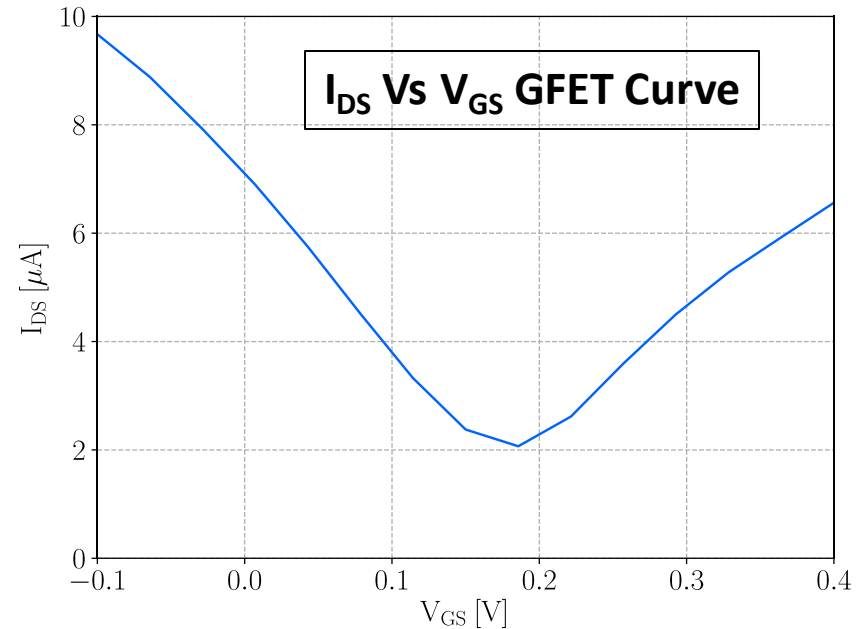
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- ▶ **Introduction**
- ▶ **Liquid-Gate GFET**
- ▶ **Time-Multiplexing**
- ▶ **ROIC**
- ▶ **DC Offset Cancellation**
- ▶ **CDS + PGA**
- ▶ **Chip**
- ▶ **Conclusions**

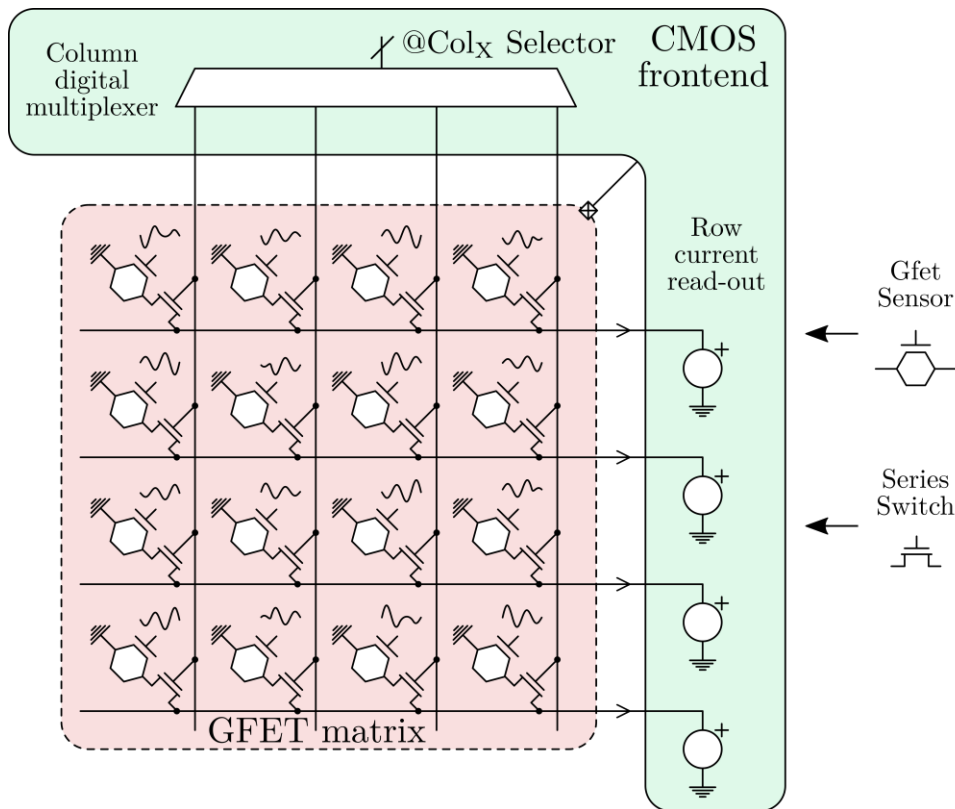
- ▶ **Low-power ICs with massive number of channels needed for neural recording**
- ▼ **Monolithical high density in small areas, high fabrication cost and low scalability**
- ▶ **Hybrid (sensors+IC) device preferred for large sensing area, low cost, CMOS compatibility and flexible substrates**
- ▲ **New Hybrid multiplexing scheme for low cost and large area flexible GFET active sensor arrays**



- ▲ **Liquid-gate** Graphene field-effect transistors (GFETs) are **good candidates for micro-electrocorticography ( $\mu$ ECOG)**
- ▲ **Good** Signal-to-Noise Ratio (SNR) while keeping **biocompatibility, low dimensionality** and **mechanical flexibility**
- ▲ **Active sensor** with an expected transconductance of  **$G_m = 0.1$  mS** and  **$R_{ds}$  of  $\sim 2$  kOhm**
- ▼ **GFET ambivalent conduction** requires from **second technology for multiplexing**



## ▶ Classic Time-Domain Multiplexing

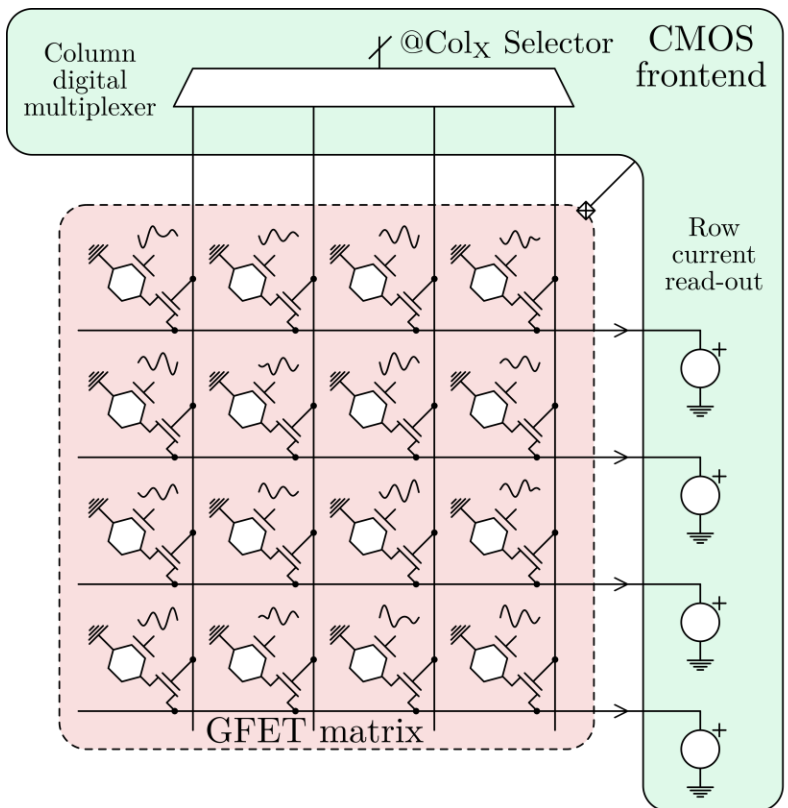


▼ **GFET + Switch** Technology integration

▲ At any time only **one device connected per row**

# Time-Multiplexing

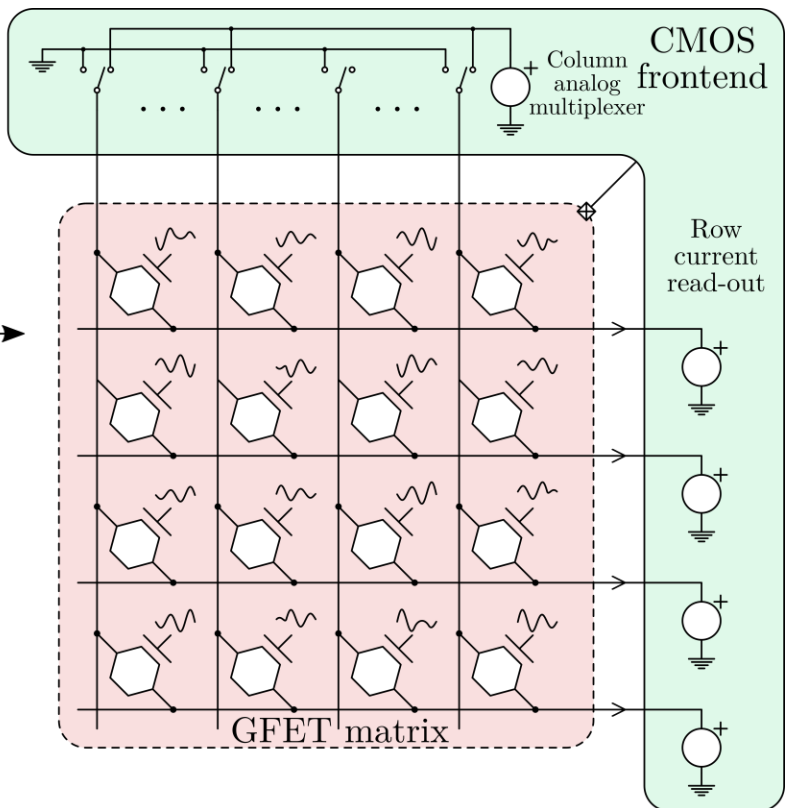
## ▶ Classic Time-Domain Multiplexing



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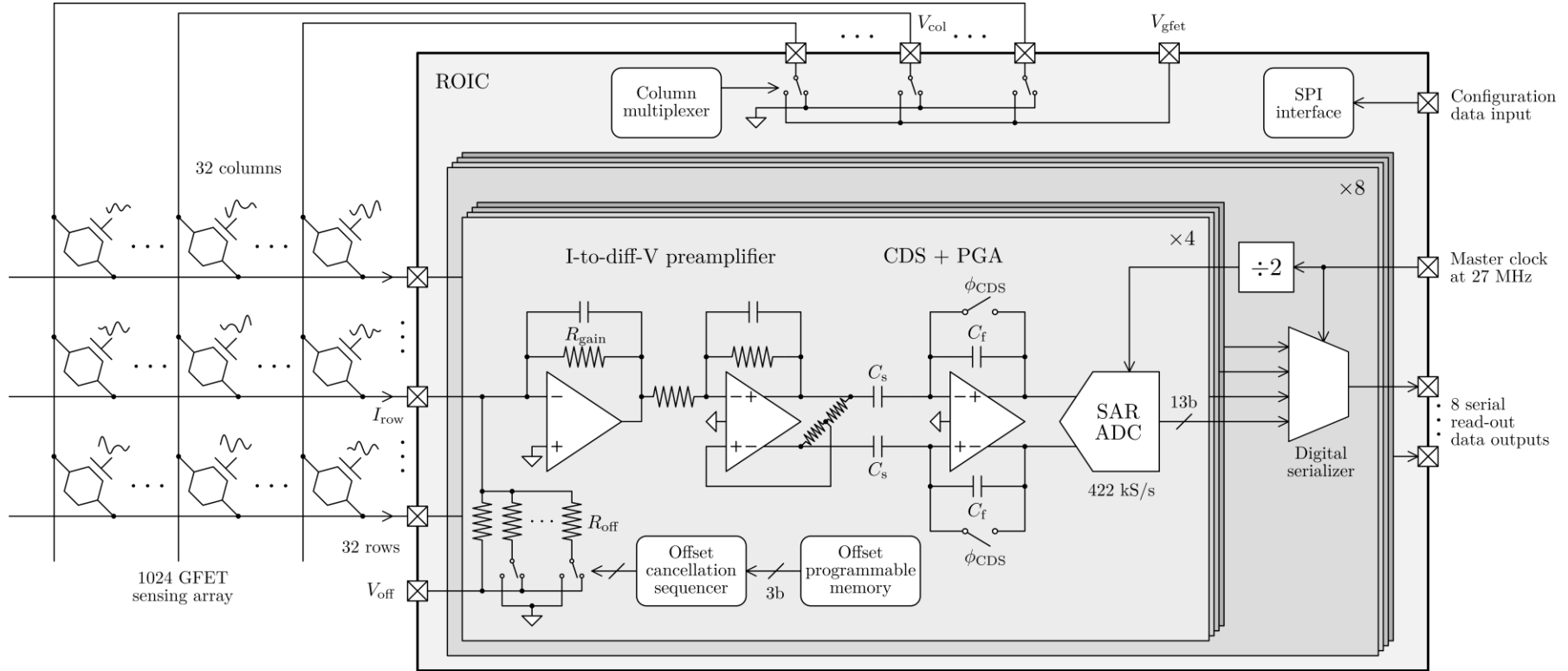
## ▶ Proposed Time-Domain Multiplexing



▲ **On-chip cmos switch** for multiplexing

▼ **Pre-Amplifier Noise Figure Loss due to GFET permanent connection**

## ► Architecture



► On-Chip cmos switch

► Transimpedance Amplifier ( $R_{GAIN} = 25 \text{ kOhm}$ )

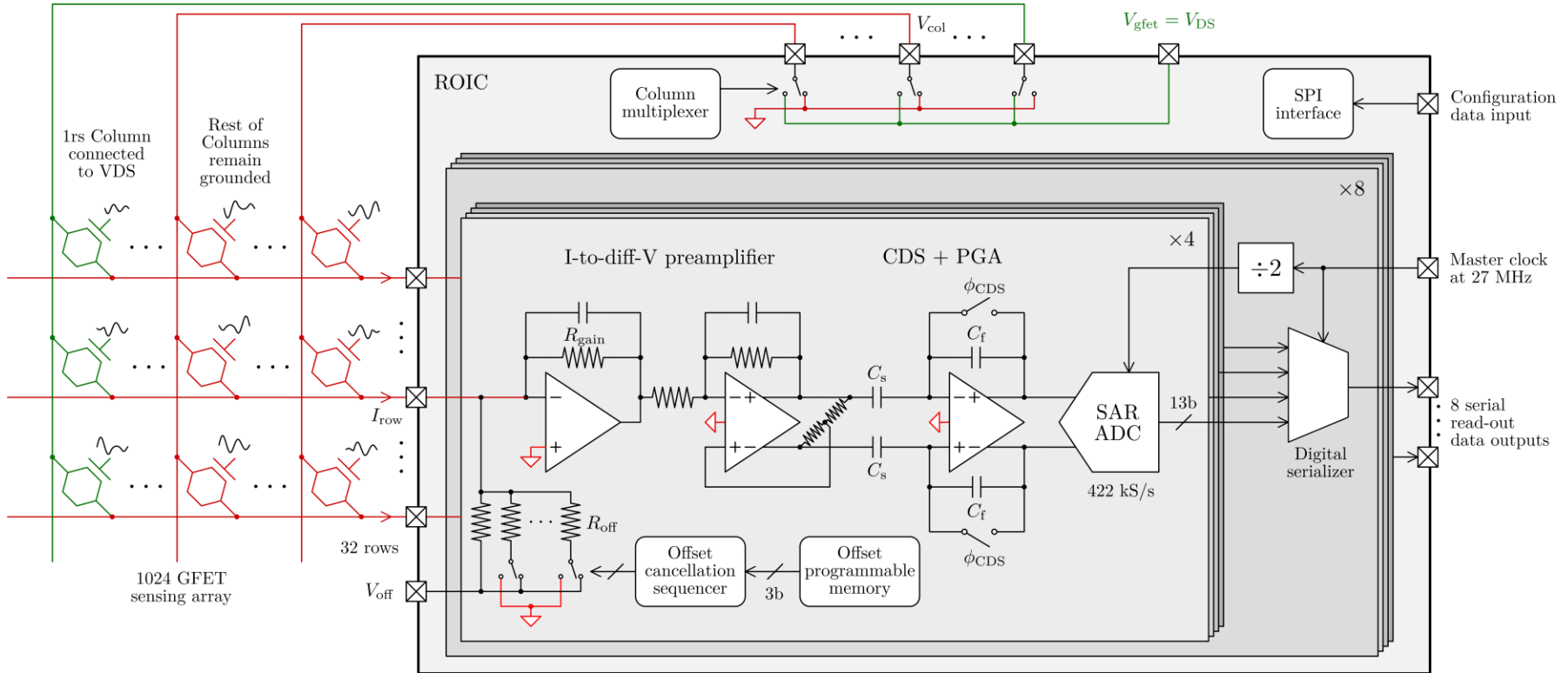
► Offset Cancellation 3-Bit R-DAC

► Single-to-Differential Amplifier

► Programmable Gain Amplifier + CDS

► SAR ADC 10 Bit ENOB

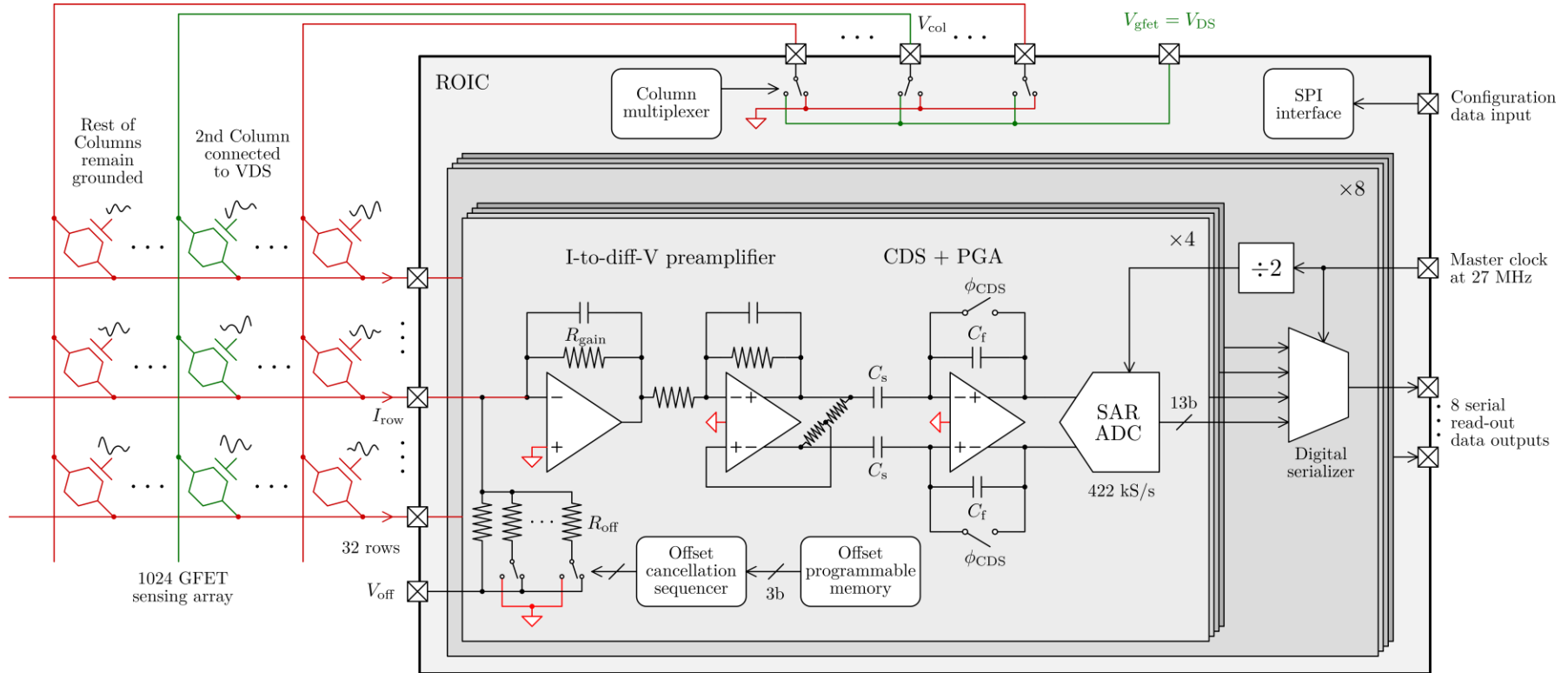
## ► Operation



- Channel multiplexing controlled by changing  $V_{DS}$  of selected column
- One Column selected at a given time (array power consumption limited to 32 GFETS)
- Remaining Columns biased to ground by the respective Transimpedance amplifier



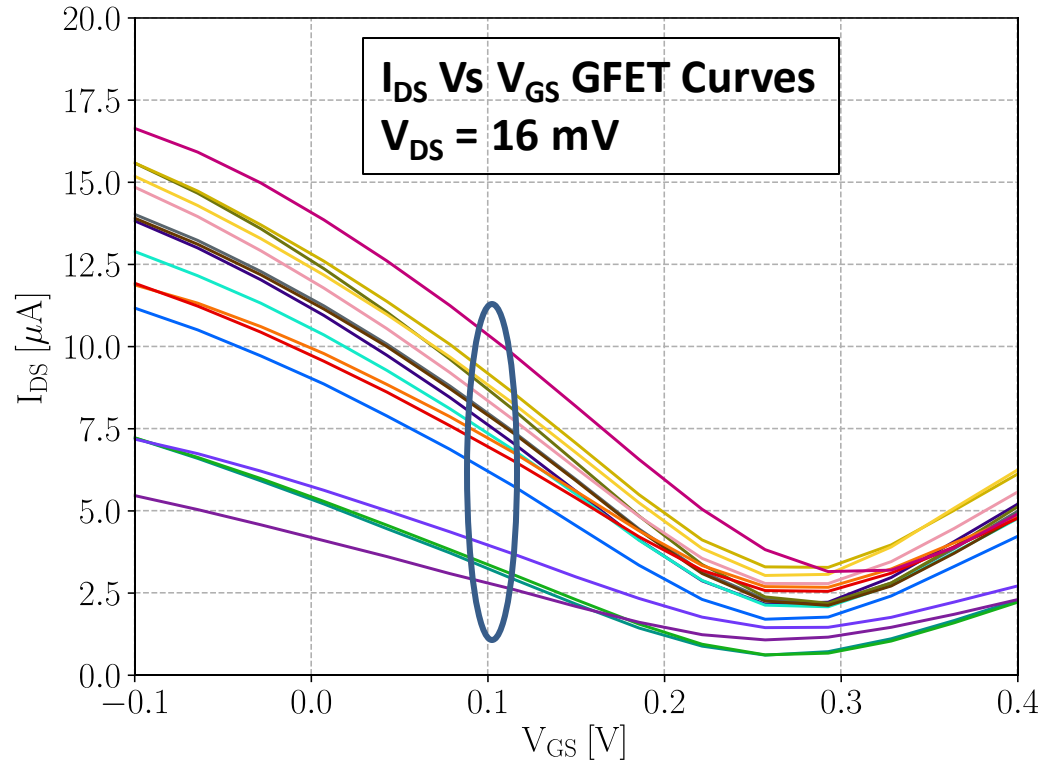
## ► Operation



## ► Two Challenges:

- ▼ AFE Noise figure loss due to GFET Up-Scaling
- ▼ GFET  $R_{DS}$  variability and DC Offset

# DC Offset Cancellation



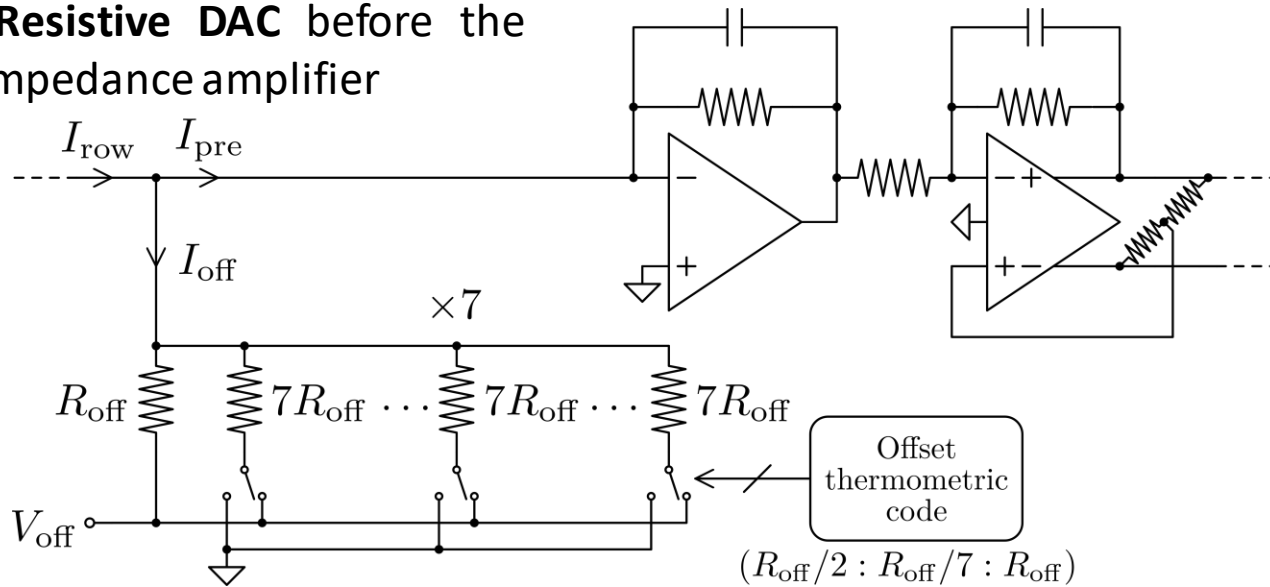
► **ROIC is a Fully DC coupled** adquisition system with **limited Input Full-Scale of 20  $\mu\text{A}$**

▼ **DC Offset: GFET  $R_{DS} = 2 \text{ k}\Omega$**  and a  **$V_{DS} = 100\text{mV}$**  a current of **50  $\mu\text{A}$**  is expected

▼ **Bio-Signal: GFET  $G_m = 0.1 \text{ mS}$**  and  **$V_{GS} = 10 \text{ mV}$**  a maximum input current of **1  $\mu\text{A}$**  is expected

► **Trade-Off: High Transresistance** needed for **Bio-Signal amplification** but **DC Offset** must be **cancelled to avoid saturation**

► **3-Bit Resistive DAC** before the transimpedance amplifier

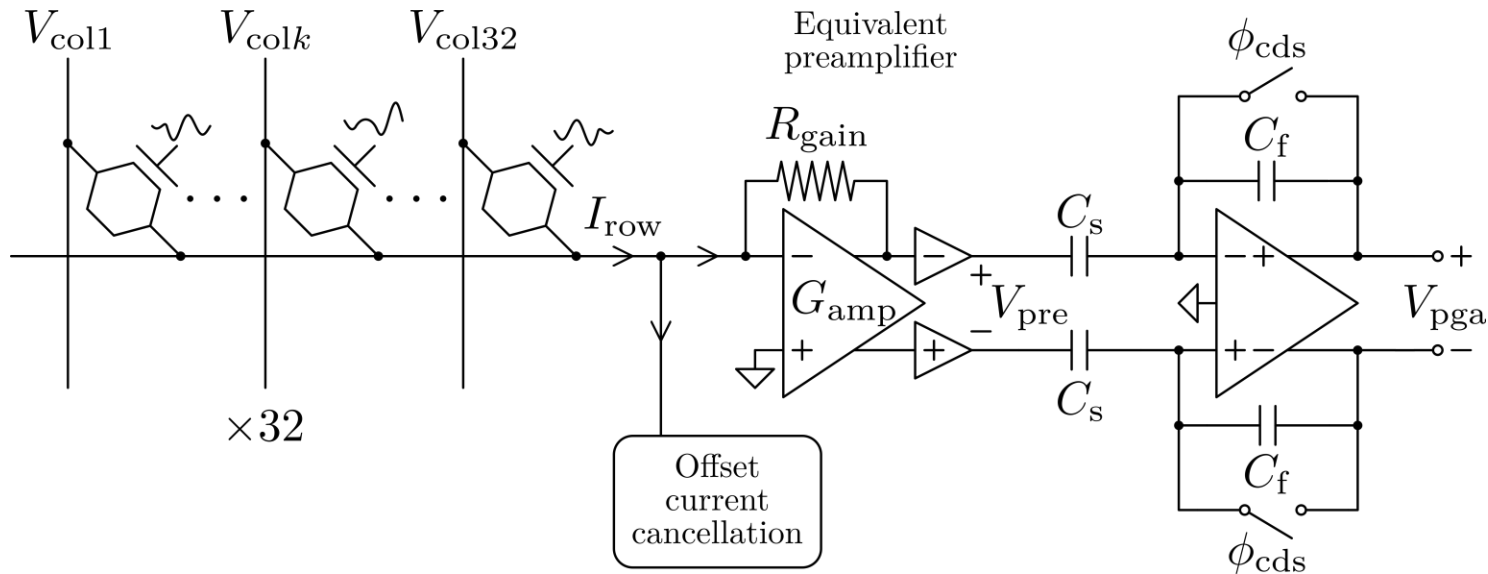


- ▲ Prevents saturation by subtracting the corresponding DC Current
- ▲ Covering a mismatch of  $\pm 30\%$  on 5% Steps from the Typ. 2 k $\Omega$  GFET
- ▲ Individual Offset cancellation configuration for each recording site (Offset configuration map)

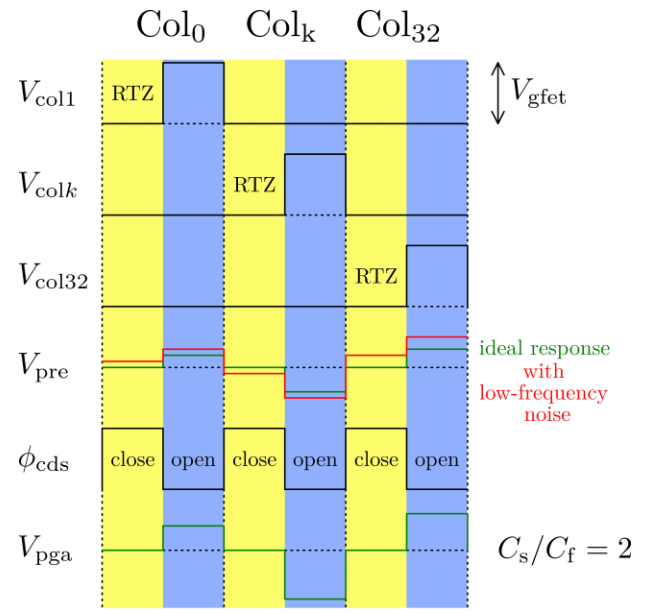
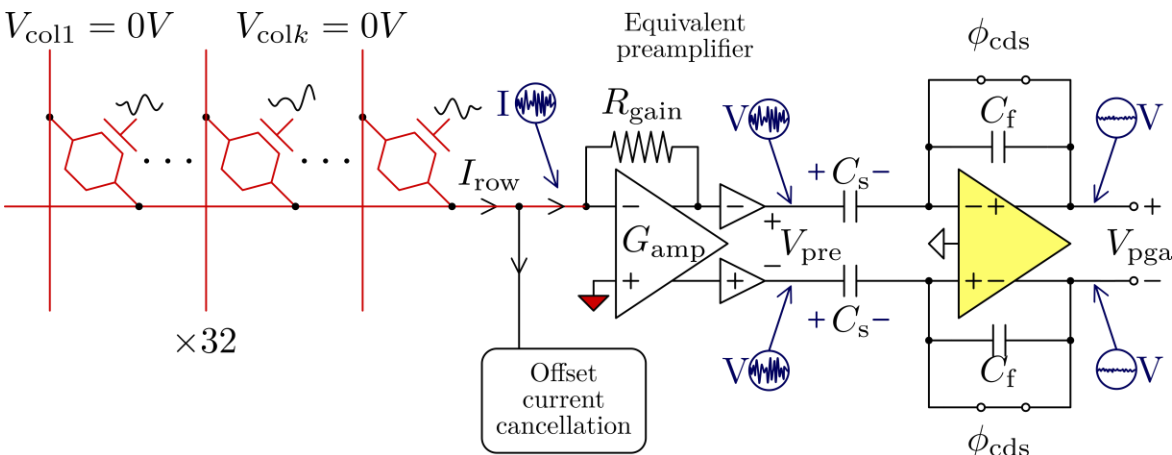
## ▼ Transimpedance noise figure loss due to GFET permanent connection

$$\text{NTF} = \frac{1}{1+G_{\text{amp}}H} \sim \frac{1}{G_{\text{amp}}H} \quad H = \frac{R_{\text{gfet}}/32}{R_{\text{gfet}}/32+R_{\text{gain}}} \simeq \frac{1}{32} \frac{R_{\text{gfet}}}{R_{\text{gain}}} \simeq \frac{1}{400}$$

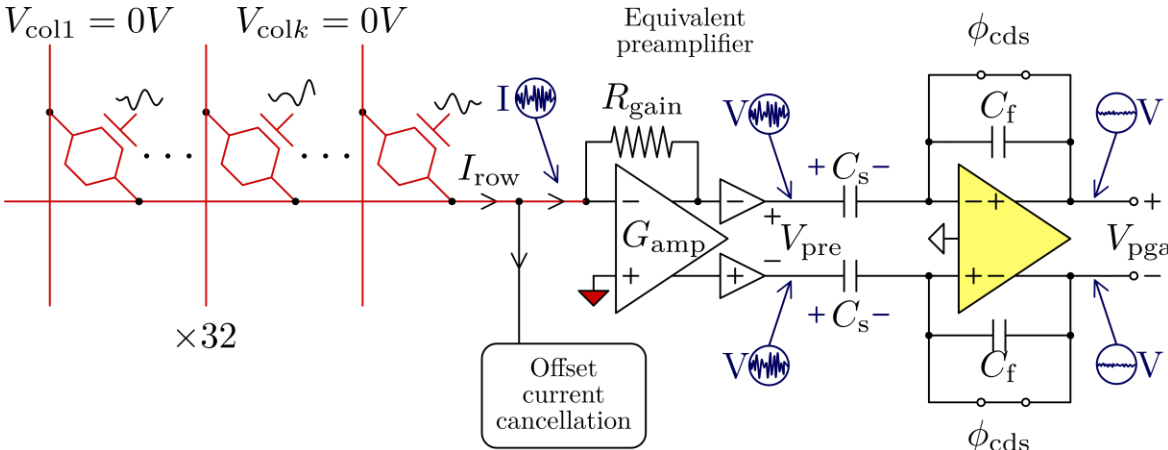
## ► Analog-Front-End



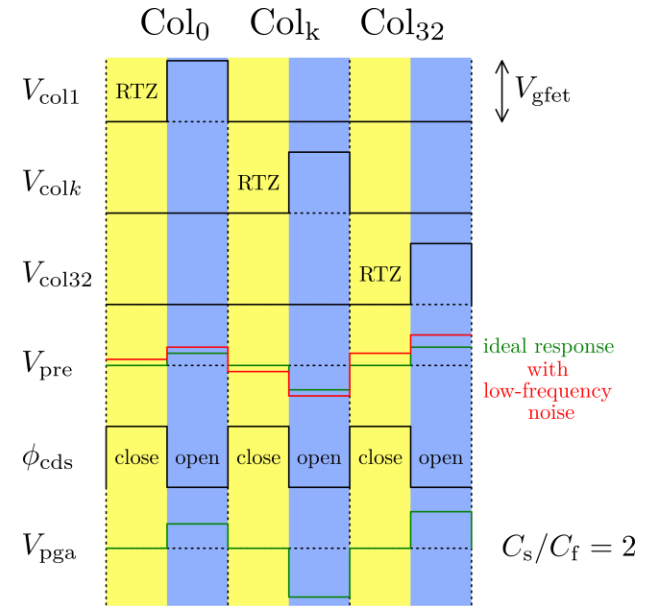
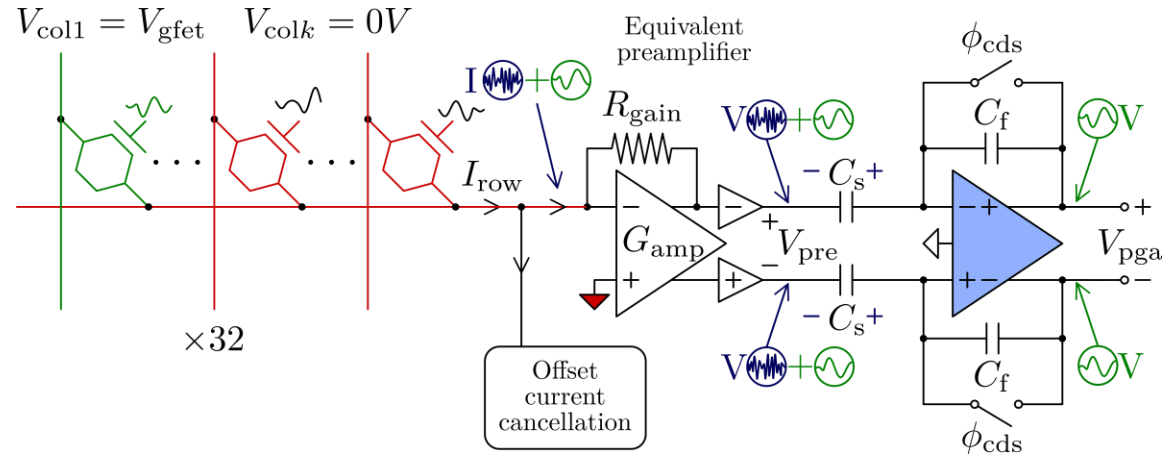
## Return-to-Zero Phase



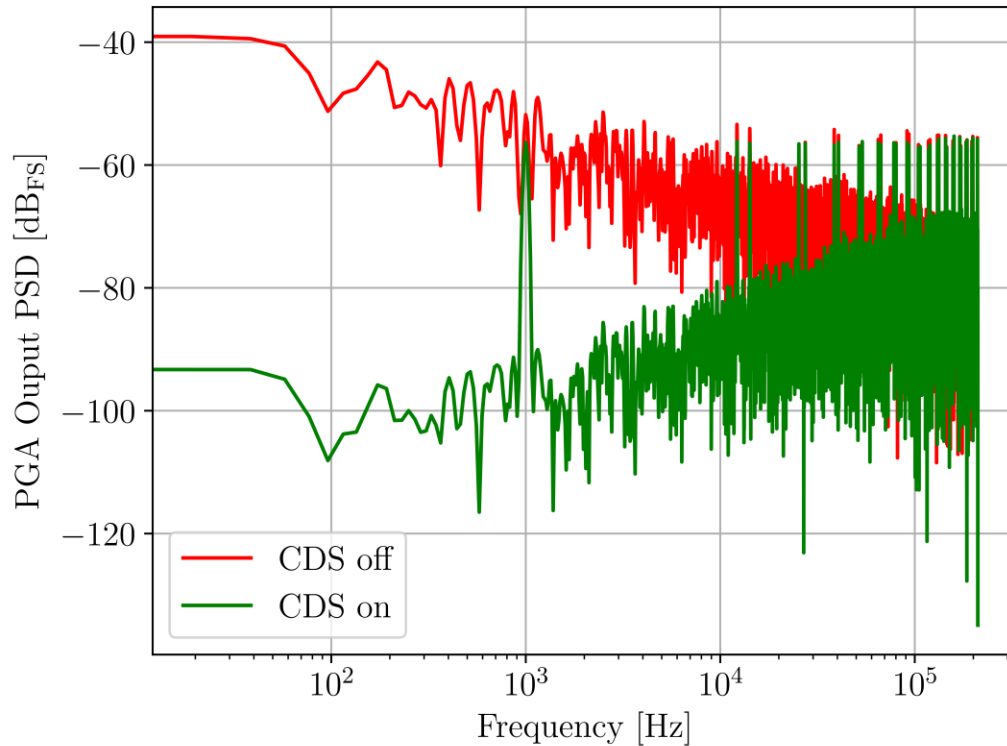
## Return-to-Zero Phase



## Amplification Phase

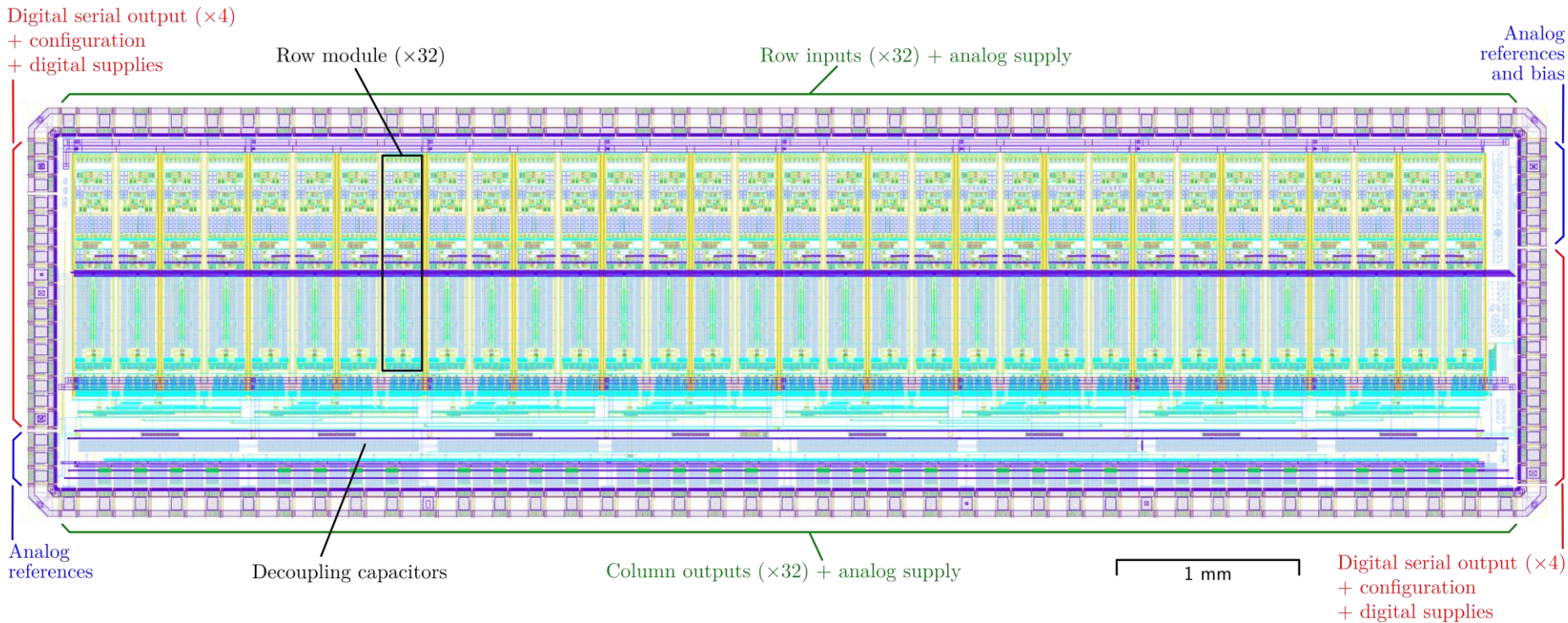


## ▶ CDS PSD



- ▲ Low-Frequency Noise from AFE cancelled
- ▲ Overall AFE still DC Coupled
- ▲ CDS circuit reuses the discrete Switched-Capacitor PGA stage

## ▲ 18.1 mm<sup>2</sup> ASIC Integrated in 1.8V 0.18 μm 1P6M MIM XFAB





## 1024-CHANNEL ROIC POST-LAYOUT SIMULATION RESULTS.

Parameter	Value	Units
Row preamp	transresistance	25 k $\Omega$
	equiv. input offset	< 1 mV <sub>rms</sub>
Row PGA	voltage gain	2 / 4 / 8 / 16 -
	CDS output noise	< 2 mV <sub>rms</sub>
Row ADC	diff. full scale	2 V <sub>pp</sub>
	sampling rate	422 kS/s
	per channel	13.2
	dynamic range	13 ENOB
Digital I/O	input	1 SPI
	output	8 serial
	speed	27 Mbps
Supply	voltage	$\pm 0.9$ V
	analog ref.	$\pm 0.5$
Power consumption	preamplifier	800 $\mu$ W
	PGA	260
	SAR ADC	80
	per channel	36
Silicon area	chip	18.7 mm <sup>2</sup>
	per channel	0.018

- ▲ High Transresistance
- ▲ 4 PGA Gains (1 Decade)
- ▲ 2Vp-p Differential FS from 1.8 V
- ▲ 6.6 kHz Bandwidth/Ch
- ▲ 1 SPI for PGA gain configuration, Offset cancellation map and TDM column Scan
- ▲ Output Data rate 216 Mbps
- ▲ Power consumption 36  $\mu$ W/Ch
- ▲ Area 0.018 mm<sup>2</sup>/Ch

- ▲ **1024-channel modular  $\mu$ ECoG ROIC with liquid-gate GFETs**
- ▲ **Novel multiplexing scheme with strong sensor-to-circuit connectivity reduction for low-cost integration and low-power operation**
- ▲ **Mixed-signal ROIC architecture capable for GFET mismatch and preamplifier noise figure loss compensation**

# Thanks for your attention!

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